

FORM PTO-1449 (Modified)		JAN 03 2001		Attorney Docket No.: 16301-028300US		Application No.: 09/632,425	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Fabrice Geiger et al.		Group: Unassigned	
				Filing Date: August 4, 2000		JAN 10 2001	
Reference Designation		U.S. PATENT DOCUMENTS				Page 1	
Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)	
L AA	5,804,509	9/8/98	Cho	438	790	3/4/96	
L AB	5,789,819	8/4/98	Gnade et al.	257	759	6/7/95	
L AC	5,753,564	5/19/98	Fukada	437	238	6/7/95	
L AD	5,668,398	9/16/97	Havemann et al.	257	522	4/12/96	
L AE	5,660,895	8/26/97	Lee et al.	427	579	4/24/96	
L AF	5,656,337	8/12/97	Park et al.	427	539	8/31/94	
L AG	5,571,576	11/5/96	Qian et al.	427	574	2/10/95	
L AH	5,561,318	10/1/96	Gnade et al.	257	638	6/7/95	
L AI	5,554,570	9/10/96	Maeda et al.	437	235	1/9/95	
L AJ	5,536,681	7/16/96	Jang et al.	437	495	6/23/95	
L AK	5,525,551	6/11/96	Ohta	437	238	6/7/94	
L AL	5,504,042	4/2/96	Cho et al.	437	247	6/23/94	
L AM	5,494,858	2/27/96	Gnade et al.	437	231	6/7/94	
L AN	5,488,015	1/30/96	Havemann et al.	437	195	5/20/94	
L AO	5,486,492	1/23/96	Yamamoto et al.	437	192	10/29/93	
L AP	5,484,749	1/16/96	Maeda et al.	437	238	4/4/95	
L AQ	5,472,913	12/5/95	Havemann et al.	437	195	8/5/94	
L AR	5,470,802	11/28/95	Gnade et al.	437	238	5/20/94	
L AS	5,461,003	10/24/95	Havemann et al.	437	187	5/27/94	
L AT	5,426,076	6/20/95	Moghadam	437	238	7/8/93	
L AU	5,399,389	3/21/95	Hieber et al.	427	579	7/20/93	
L AV	5,393,708	2/28/95	Hsia et al.	437	228	10/8/92	
L AW	5,356,722	10/18/94	Nguyen et al.	427	569	6/10/92	
L AX	5,271,972	12/21/93	Kwok et al.	427	579	8/17/92	
L AY	5,094,972	3/10/92	Pierce et al.	437	67	6/14/90	
L AZ	4,992,306	2/12/91	Hochberg et al.	427	255.3	2/1/90	
L BA	4,971,655	11/20/90	Stefano et al.	156	659.1	12/26/89	
L BB	4,962,064	10/9/90	Haskell et al.	437	228	5/12/88	
L BC	4,851,370	7/25/89	Doklan et al.	437	225	12/28/87	
L BD	4,789,648	12/6/88	Chow et al.	437	225	10/28/85	
L BE	4,614,021	9/30/86	Hulseweh	29	590	3/29/85	
FOREIGN PATENT DOCUMENTS							
	Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)	
L BF	EP 822 585	2/4/98	Europe				
L BG	JP 11-097533	4/9/99	Japan			Abstract Only	

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		Filing Date: August 4, 2000	Up: Unassigned
		TC 1700	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
<u>L</u> BH	Fisher et al., "Global Planarization by Selective Deposition of Ozone/Teos," from VMIC conference, pages 247-253 (1995).		
<u>L</u> BI	Fujino et al., "Surface Modification of Base Materials for TEOS/O ₃ Atmospheric Pressure Chemical Vapor Deposition," <u>J. Electrochem. Soc.</u> , 139(6):1690-1692 (1992).		
<u>L</u> BJ	Fujino et al., "Dependence of Deposition Characteristics on Base Materials in TEOS and Ozone CVD at Atmospheric Pressure," <u>J. Electrochem. Soc.</u> , 138(2):550-554 (1991).		
<u>L</u> BK	Gaillard et al., "Silicon dioxide chemical vapor deposition using silane and hydrogen peroxide," <u>J. Vac. Sci. Technol. B.</u> , 14(4):2767-2769 (1996).		
<u>L</u> BL	Kishimoto et al., "Planarized SiO ₂ Interlayer Formed by Two Step O ₃ /TEOS APCVD and Low Temperature Annealing," <u>Proceedings of the International VLSI Multilevel Interconnection Conferences</u> , VMIC Conference, Santa Clara, CA - June 9-10, 1992, pgs. 149-155 (1992).		
<u>L</u> BM	Kwok et al., "Surface Related Phenomena in Integrated PECVD/Ozone-TEOS SACVD Processes for Sub-Half Micron Gap Fill: Electrostatic Effects," <u>J. Electrochem. Soc.</u> , 141(8):2172-2177 (1994).		
<u>L</u> BN	Lee et al., "SACVD: A New Approach for 16Mb Dielectrics," <u>Semiconductor International</u> , pgs. 116-120 (1992).		
<u>L</u> BO	S. Mokhtari et al., "Mechanisms of Deposition of SiO ₂ from TEOS and Related Organosilicon Compounds and Ozone," <u>J. Electrochem. Soc.</u> , 142(7):2332-2340 (1995).		
<u>L</u> BP	Ogawa et al., "Novel ARC Optimization Methodology for KrF Excimer Laser Lithography at Low K1 Factor," <u>Proceedings SPIE—The International Society for Optical Engineering, Optical/Laser Microlithography V</u> , eds. Cuthbert, 1674(1):362-375 (1992).		
<u>L</u> BQ	Park et al., "A Void-free Gap Fill Technology using APCVD TEOS-O ₃ Oxide," from DUMIC conference, pages 183-185 (1997).		
<u>✓</u> BR	Saito et al., "Pressure-Controlled Two-Step TEOS-O ₃ CVD Eliminating the Base Material Effect," <u>1995 Symposium on VLSI Technology Digest of Technical Papers</u> , pages 43-44 (1995).		
<u>✓</u> BS	Sato et al., "Improvement of Gap-Filling Property of O ₃ -tetraethylorthosilicate (TEOS) Film by Ethanol Surface Treatment," <u>Jpn. J. Applied Physics</u> , vol. 32, part 2, No. 1A/B, pages L110-L112 (1993).		
EXAMINER	DATE CONSIDERED 1/6/2		

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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